

Amendments to the Claims:

Please cancel claims 78 and 79 and 81-94, and amend claim 73 as follows:

Listing of Claims:

1-72. (Cancelled)

73. (Currently Amended) An in-process device, comprising:

a substrate; [[and]]

a conductive layer comprising a metal layer over the substrate, the
conductive layer being exposed to a material selected from the group consisting of phosphine
and methylsilane to reduce an ability of the conductive layer to associate with oxygen[.]; and
a second conductive layer comprising a tungsten nitride layer
formed on the conductive layer and a third conductive layer comprising a copper layer formed on
the second conductive layer.

2 74. (Previously Presented) The in-process device of claim 73 wherein the
conductive layer comprises tungsten nitride.

3 75. (Previously Presented) The device in claim 74, further comprising another
conductive layer formed on the tungsten nitride layer.

4 76. (Cancelled)

77. (Previously Presented) The in-process device of claim 75 wherein the
other conductive layer comprises copper.

78-79. (Cancelled)

5 88 (Previously Presented) The in-process device of claim 3 wherein the substrate comprises a silicon substrate.

61 [81-94 (Cancelled)
